IN THE CLAIMS

1-18 (Withdrawn)

19-34 (Canceled)

35. (New) A method of fabricating a fluid-ejection device comprising:

forming a cavitation layer overlying a substrate in lateral contact with a first portion of dielectric layer using atomic layer deposition; and

forming a passivation layer on a second portion of the dielectric layer using atomic layer deposition, and not on the cavitation layer.

36. (New) The method of claim 35, wherein forming the passivation layer on the second portion of the dielectric layer comprises forming a carbide layer on the second portion of the dielectric layer.

37. (New) The method of claim 35, wherein forming a cavitation layer comprises adding a dopant to the cavitation layer using atomic layer deposition.

38. (New) The method of claim 35, wherein the cavitation layer is tantalum, titanium, molybdenum, or niobium.

39. (New) A method of manufacturing a print head comprising:

forming a first dielectric layer overlying at least a first portion of a substrate using atomic layer deposition;

forming a second dielectric layer having a first portion overlying at least a second portion of the substrate and a second portion overlying at least a portion of the first dielectric layer;

forming a cavitation layer overlying the first dielectric layer and in lateral contact with the first portion of the second dielectric layer using atomic layer deposition; and

forming a third dielectric layer on the second portion of the second dielectric layer using atomic layer deposition, and not on the cavitation layer.

40. (New) The method of claim 39, wherein at least one of the first and second dielectric layers is a carbide layer.

41. (New) The method of claim 39, wherein the first dielectric layer comprises a plurality of first dielectric layers, wherein at least one of the plurality of first dielectric layers is a silicon carbide layer and at least another of the plurality of first dielectric layers is a silicon nitride layer.

42. (New) The method of claim 39 further comprises:

before forming the second dielectric layer, forming a seed layer overlying the second portion of the substrate using atomic layer deposition; and

before forming the second dielectric layer, forming a conductive metal layer on the seed layer.

43. (New) The method of claim 43, wherein the conductive metal layer is aluminum or tungsten.

44. (New) The method of claim 43, wherein the conductive metal layer forms one or more contacts.

45. (New) The method of claim 39 further comprising forming a resistive layer before forming the first dielectric layer, wherein forming the first dielectric layer comprises forming the first dielectric layer on the resistive layer.